

## N-Channel 60-V (D-S) MOSFET

**PRODUCT SUMMARY**

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)	$Q_g$ (Typ)
60	0.0055 at $V_{GS} = 10$ V	90 <sup>d</sup>	78.5

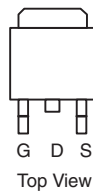
**FEATURES**

- TrenchFET<sup>®</sup> Power MOSFETS
- 175 °C Junction Temperature
- 100 %  $R_g$  and UIS Tested

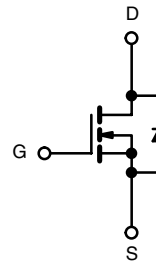

**RoHS**  
COMPLIANT

**APPLICATIONS**

- Power Supply
  - Secondary Synchronous Rectification
- Industrial

**TO-263**


Ordering Information: SUM90N06-5m5P-E3 (Lead (Pb)-free)



N-Channel MOSFET

**ABSOLUTE MAXIMUM RATINGS**  $T_C = 25$  °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current ( $T_J = 175$ °C)	$I_D$	$T_C = 25$ °C	90 <sup>d</sup>
		$T_C = 70$ °C	90 <sup>d</sup>
Pulsed Drain Current	$I_{DM}$	240	A
Avalanche Current	$I_{AS}$	50	
Single Avalanche Energy <sup>a</sup>	$E_{AS}$	125	mJ
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_C = 25$ °C	272 <sup>b</sup>
		$T_A = 25$ °C <sup>c</sup>	3.75
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 175	°C

**THERMAL RESISTANCE RATINGS**

Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) <sup>c</sup>	$R_{thJA}$	40	°C/W
Junction-to-Case (Drain)	$R_{thJC}$	0.55	

Notes:

- Duty cycle  $\leq 1$  %.
- See SOA curve for voltage derating.
- When Mounted on 1" square PCB (FR-4 material).
- Package limited.

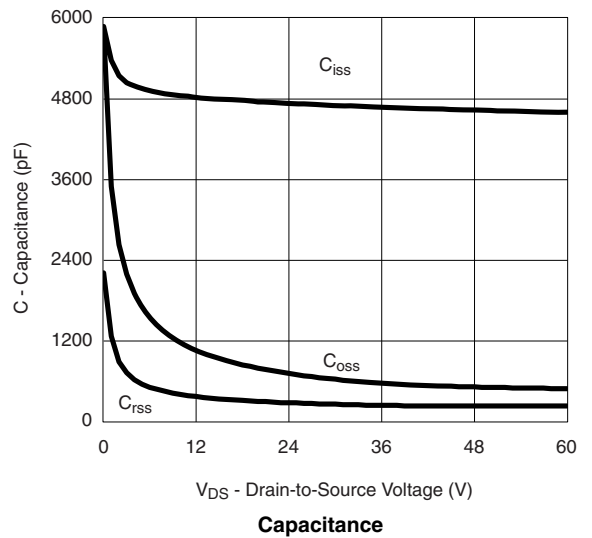
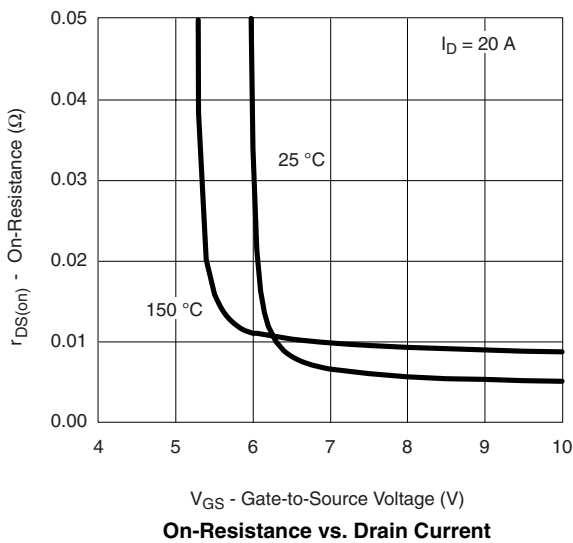
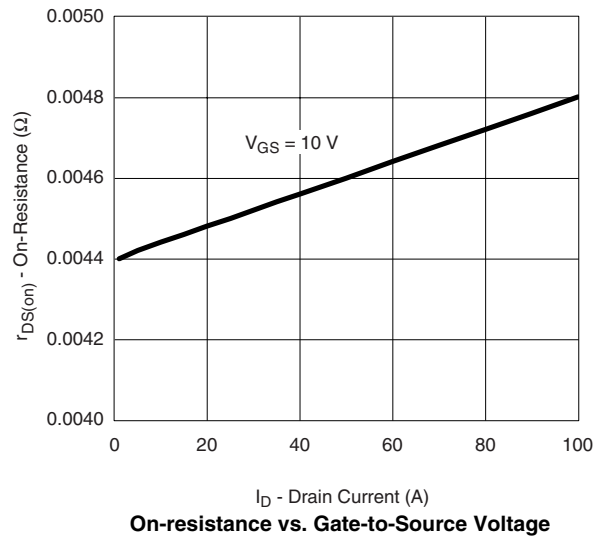
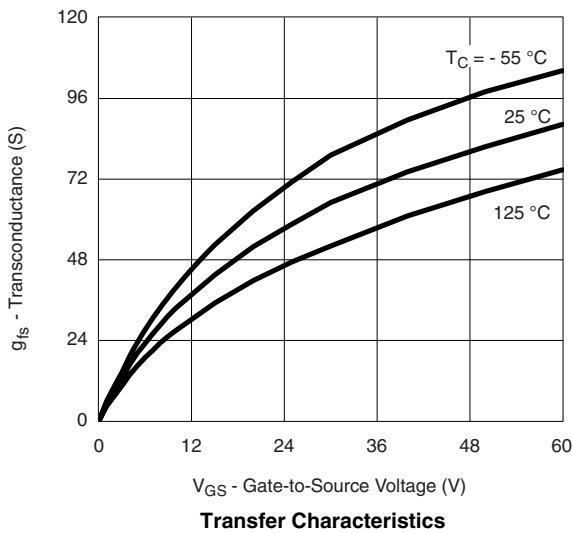
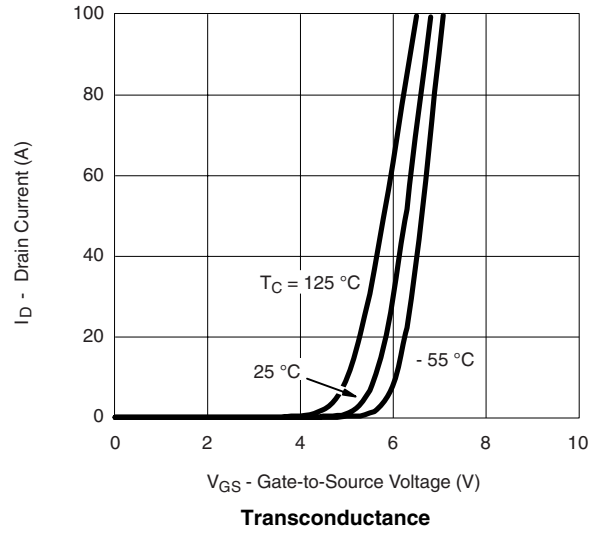
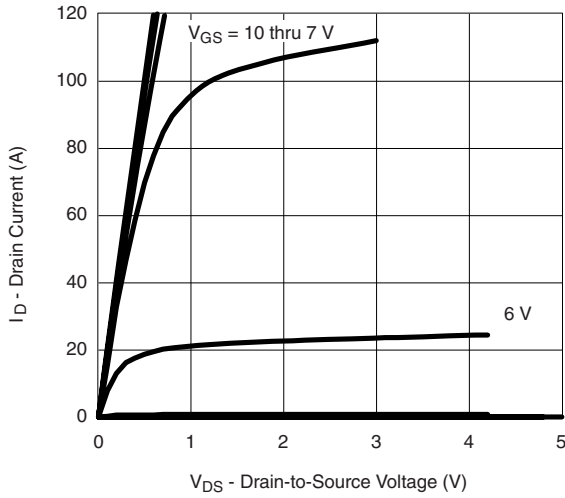
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{DS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.5		4.5	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 250$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$			250	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	70			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.0045	0.0055	$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.0072	0.009	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$		58		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V}, f = 1\text{ MHz}$		4700		pF
Output Capacitance	$C_{oss}$			620		
Reverse Transfer Capacitance	$C_{rss}$			250		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 30\text{ V}, V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		78.5	120	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			28		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			20.6		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		1.2	2.4	$\Omega$
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong 50\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		16	30	ns
Rise Time <sup>c</sup>	$t_r$			10	20	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			25	40	
Fall Time <sup>c</sup>	$t_f$			8	15	
<b>Source-Drain Diode Ratings and Characteristics</b> $T_C = 25\text{ }^\circ\text{C}$ <sup>b</sup>						
Continuous Current	$I_S$				85	A
Pulsed Current	$I_{SM}$				240	
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_F = 20\text{ A}, V_{GS} = 0\text{ V}$		0.83	1.5	V
Reverse Recovery Time	$t_{rr}$	$I_F = 75\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		62	100	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			3.8	5.7	A
Reverse Recovery Charge	$Q_{rr}$			118	180	nC

Notes:

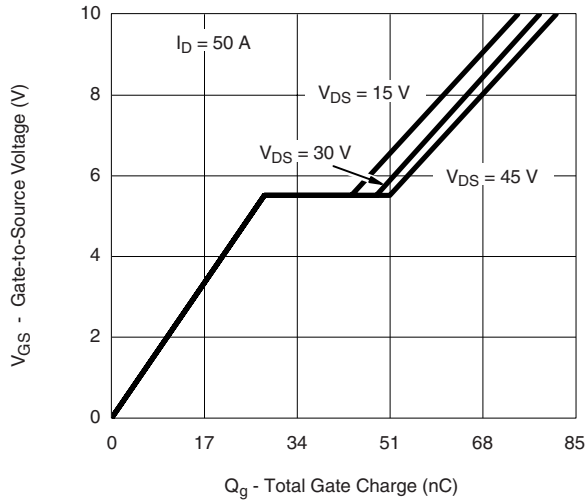
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

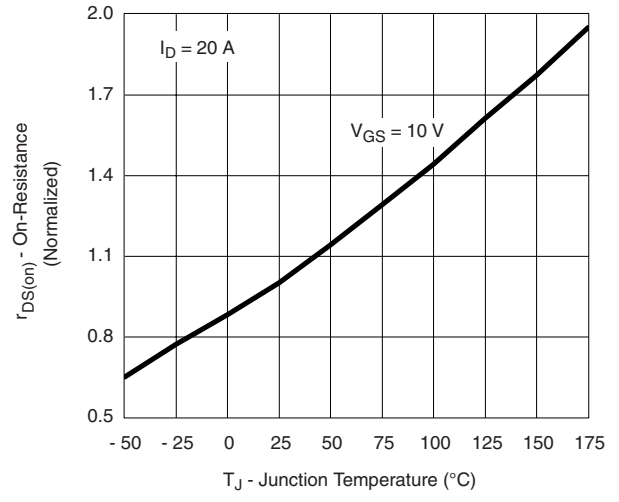
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



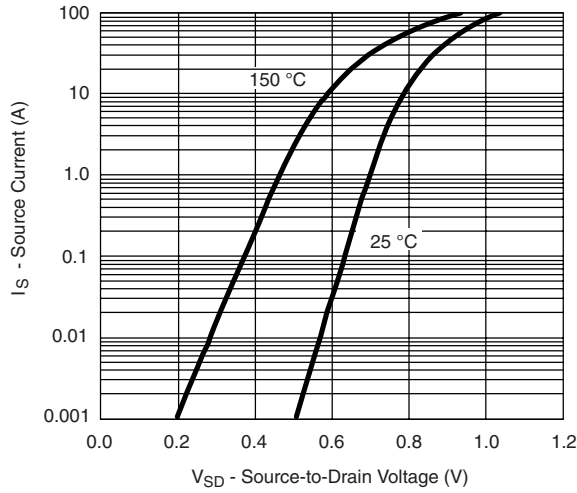
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



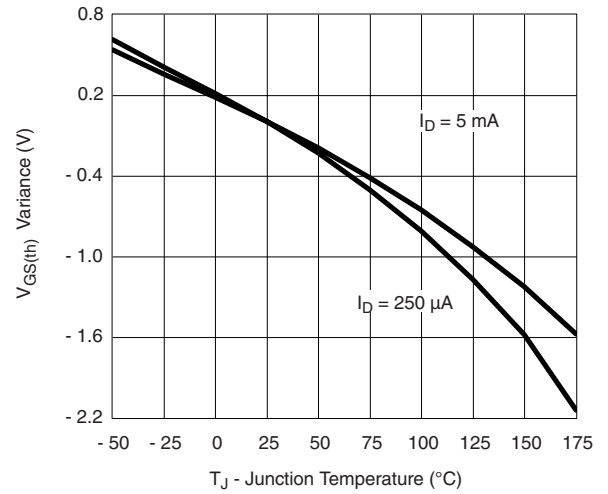
**On-Resistance vs. Junction Temperature**



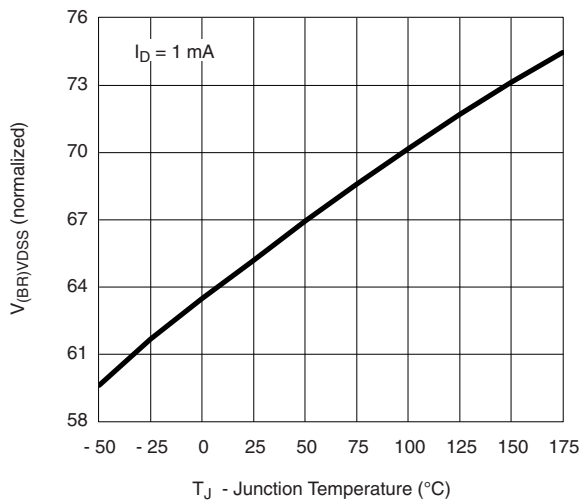
**Threshold Voltage**



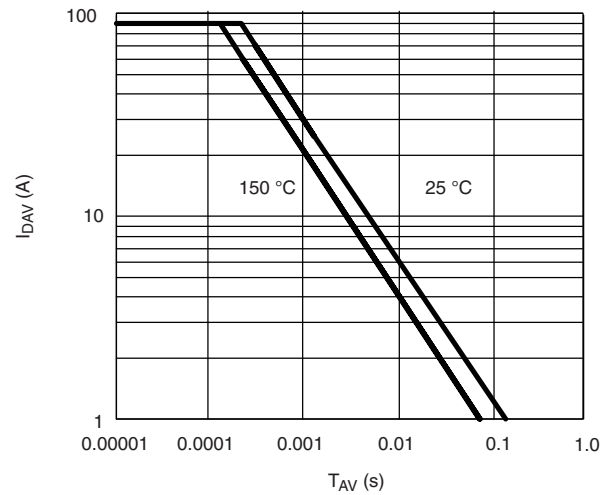
**Gate Charge**



**On-Resistance vs. Junction Temperature**

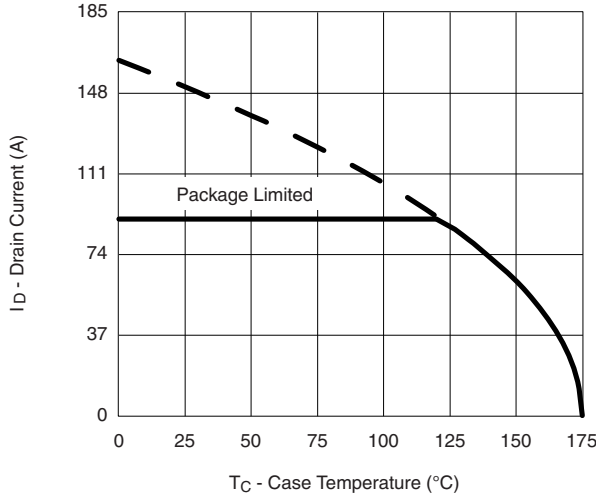


**Source-Drain Diode Forward Voltage**

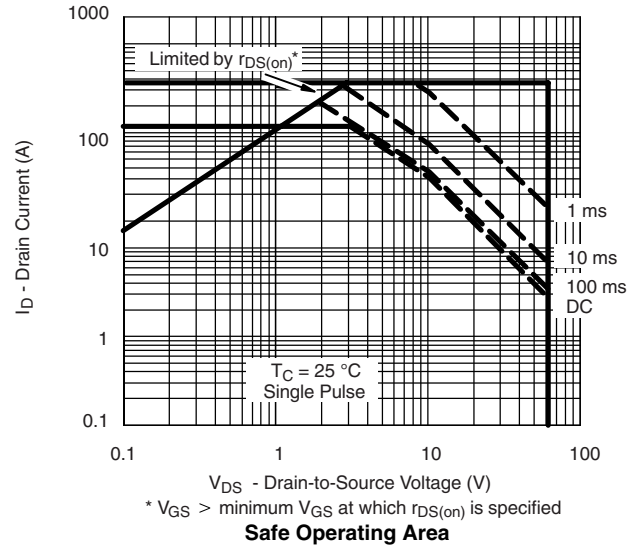


**Maximum Drain Current vs. Case Temperature**

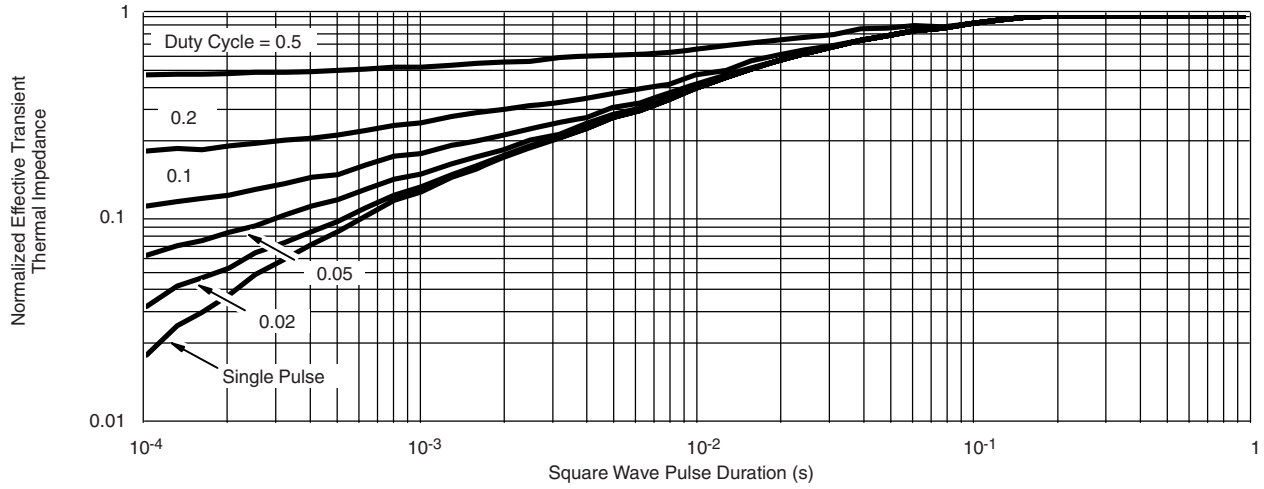
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Single Pulse Avalanche Current Capability vs. Time**



**Safe Operating Area**



**Normalized Thermal Transient Impedance, Junction-to-Case**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?69537>.



## Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.